

Please add new claims 13 and 14:

13. (New) The high resistive thin film resistor structure of claim 8, wherein the diffusion barrier layer covers an entire upper surface of the lightly doped polysilicon layer.

14. (New) The high resistive thin film resistor structure of claim 8, wherein the spacer is in contact with the sidewalls of the lightly doped polysilicon layer and the barrier diffusion layer.